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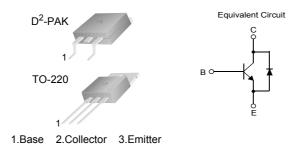
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FAIRCHILD SEMICONDUCTOR®

KSC5338D/KSC5338DW NPN Triple Diffused Planar Silicon Transistor

Features

- High Voltage Power Switch Switching Application
- Wide Safe Operating Area
- Built-in Free-Wheeling Diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time
- Two Package Choices : TO-220 or D²-PAK



Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	1000	V
V _{CEO}	Collector-Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage	12	V
Ι _C	Collector Current (DC)	5	A
I _{CP}	*Collector Current (Pulse)	10	Α
Ι _Β	Base Current (DC)	2	А
I _{BP}	*Base Current (Pulse)	4	А
P _C	Power Dissipation (T _C =25°C)	75	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 to 150	°C

* Pulse Test : Pulse Width = 5ms, Duty Cycle \leq 10%

Thermal Characteristics

Symbol	Parameter		Rating	Units
R _{θjc}	- Thermal Resistance	Junction to Case	1.65	°C/W
R _{θja}		Junction to Ambient	62.5	°C/W
Τ _L	Maximum Lead Temperatu	re for Soldering	270	°C

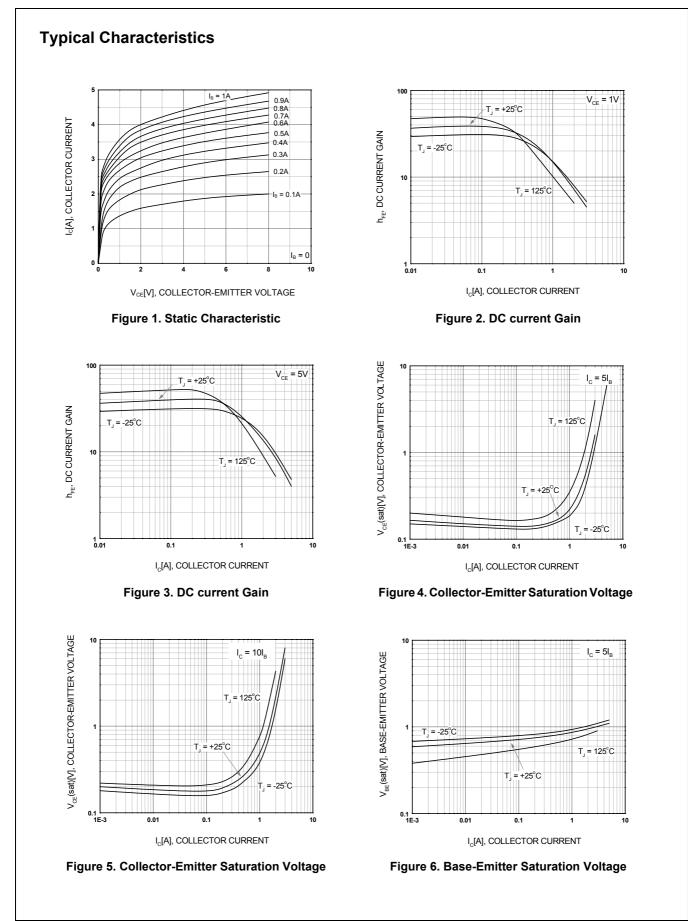
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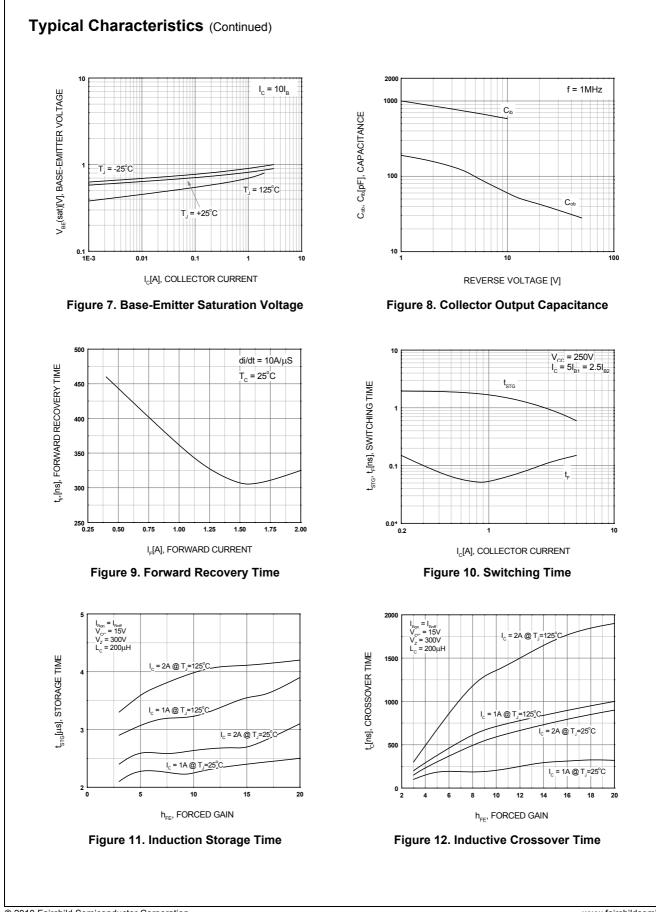
May 2010

Symbol	Parameter	Test Cond	ition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =1mA, I _E =0		1000			V
BV _{CEO}	Collector-Emitter Breakdown Voltage			450			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =1mA, I _C =0		12			V
I _{CBO}	Collector Cut-off Current	V _{CB} =800V, I _E =0				10	μA
I _{CES}	Collector Cut-off Current	V _{CES} =1000V, I _{EB} =0	T _a =25°C			100	μΑ
020			T _a =125°C			500	μΑ
I _{CEO}	Collector Cut-off Current	V _{CE} =450V, I _B =0	T _a =25°C			100	μA
020			T _a =125°C			500	μA
I _{EBO}	Emitter Cut-off Current	V _{EB} =10V, I _C =0	u			10	μA
h _{FE}	DC Current Gain	V _{CE} =1V, I _C =0.8A	T _a =25°C	15	25		
. –				10	14		
		V _{CE} =1V, I _C =2A	T _a =25°C	6	9		
		OL / O		4	6		
		V _{CE} =2.5V, I _C =1A	T _a =25°C	18	25		
			T _a =125°C	14	18		
V _{CF} (sat)	Collector-Emitter Saturation Voltage	I _C =0.8A, I _B =0.08A	T _a =25°C		0.35	0.5	V
OL(11)			T _a =125°C		0.55	0.75	V
		I _C =2A, I _B =0.4A	T _a =25°C		0.47	0.75	V
			T _a =125°C		0.9	1.1	V
		I _C =0.8A, I _B =0.04A			0.9	1.5	V
			T _a =125°C		1.8	2.5	V
		I _C =1A, I _B =0.2A	T _a =25°C		0.22	0.5	v
		.С. н., .В. с. <u>–</u> . с	T _a =125°C		0.3	0.6	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C =0.8A, I _B =0.08A	T _a =25°C		0.8	1.0	V
BE(out)			T _a =125°C		0.65	0.9	V
		I _C =2A, I _B =0.4A	T _a =25°C		0.9	1.0	V
		1C 27 (, 1B 0.17 (T _a =125°C		0.8	0.9	v
C _{ib}	Input Capacitance	V _{EB} =10V, I _C =0.5A,	ŭ		550	750	pF
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1			60	100	pF
f _T	Current Gain Bandwidth Product	I _C =0.5A,V _{CE} =10V			11	100	MHz
V _F	Diode Forward Voltage	I _F =1A, I _C =1mA,	T _a =25°C		0.86	1.3	V
۷F	blode i of ward voltage	I _E =0	T _a =125°C		0.79	1.0	v
		I _F =2A	T _a =25°C		0.95	1.5	V
			T _a =125°C		0.88	1.0	V
t _{fr}	Diode Forward Recovery Time	I _F =0.4A	1a-120 0		460		ns
٩r	(di/dt=10A/µs)	I _F =1A			360		ns
		I _F =2A			325		ns
CE(DSAT)	Dynamic Saturation Voltage	I _C =1A, I _{B1} =100mA V _{CC} =300V at 1 μs	T _a =25°C		8		V
			T _a =125°C		15		V
		I _C =1A, I _{B1} =100mA	T _a =25°C		2.9		V
		V_{CC} =300V at 3 µs	T _a =125°C		8		V
		I _C =2A, I _{B1} =400mA V _{CC} =300V at 1 μs	T _a =25°C		9		V
			T _a =125°C		17		V
		I _C =2A, I _{B1} =400mA	T _a =25°C		1.9		V
		V_{CC} =300V at 3 µs		1	8.5	1	V

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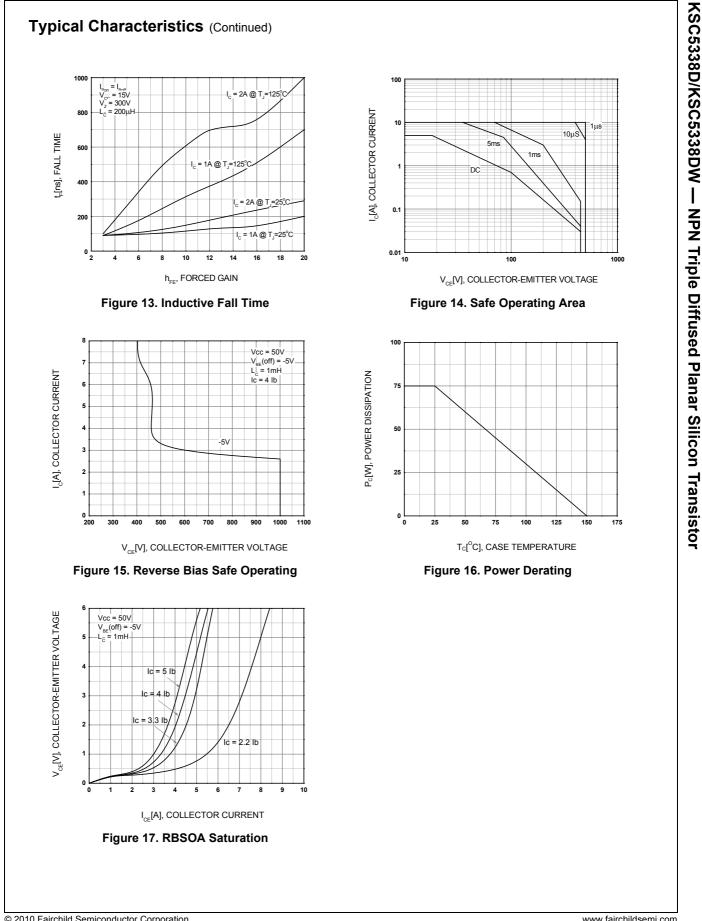
Symbol	Parameter	Test Co	ndition	Min	Тур.	Max.	Units
ESISTIVE	LOAD SWITCHING (D.C < 10%	, Pulse Width=40µs)					1
t _{ON}	Turn On Time	I _C =2.5A, I _{B1} =50	0mA,		500	750	ns
t _{STG}	Storage Time	I _{B2} =-1A, V _{CC} =2	50V, R _L = 100Ω	1.2		1.5	μS
t _F	Fall Time		-		100	200	ns
t _{ON}	Turn On Time	I _C =2A,	T _a =25℃		100	150	ns
011		I _{B1} =400mA,	T _a =125°C		150		ns
t _{STG}	Storage Time	I _{B2} =-1A,	T _a =25℃		1.4	2.2	μS
010		V _{CC} =300V, R _I = 150Ω	T _a =125°C		1.7		μs
t _F	Fall Time		T _a =25℃		90	150	ns
·			T _a =125°C		150		ns
t _{ON}	Turn On Time	I _C =2.5A,	T _a =25°C		120	150	ns
0N		I _{B1} =500mA,	T _a =125°C		150		ns
t _{STG}	Storage Time	I _{B2} =-5mA,	T _a =25℃	1.8		2.1	μS
010		V _{CC} =300V, R _I = 120Ω	T _a =125℃		2.6		μS
t _F	Fall Time	1(1 = 12022	T _a =25°C		110	150	ns
1			T _a =125°C		160		ns
NDUCTIVE	LOAD SWITCHING (V _{CC} =15V)		a				
t _{STG}	Storage Time	I _C =2.5A,	T _a =25℃		1.9	2.2	μS
010		I _{B1} =500mA,			2.4		μS
t _F	Fall Time	I _{B2} =-0.5A,	T _a =25°C		160	200	ns
1		V _Z =350V, L _C =300μH	T _a =125°C		330		ns
t _C	Cross-over Time	Ες=300μΠ	T _a =25°C		350	500	ns
-0			T _a =125°C		750		ns
t _{STG}	Storage Time	I _C =2A,	T _a =25°C	1.95		2.25	μS
-316		I _{B1} =400mA,	T _a =125°C		2.9		μS
t⊨	Fall Time	I _{B2} =-0.4A,	T _a =25°C		120	150	ns
4		V _Z =300V, L _C =200μH	T _a =125°C		270		ns
t _C	Cross-over Time	ις-200μπ	T _a =25°C		300	450	ns
-0			T _a =125°C		700		ns
t _{STG}	Storage Time	I _C =1A,	T _a =25°C		0.6	0.8	μS
-316		I _{B1} =100mA,	T _a =125°C		1.0		μο
t _F	Fall Time	I _{B2} =-0.5A,	T _a =25°C		70		ns
Ŧ		V _Z =300V,	T _a =125°C		110		ns
t _C	Cross-over Time	L _C =200μΗ	T _a =25°C		80	130	ns
•U			T _a =25 ℃ T _a =125°C		170		ns



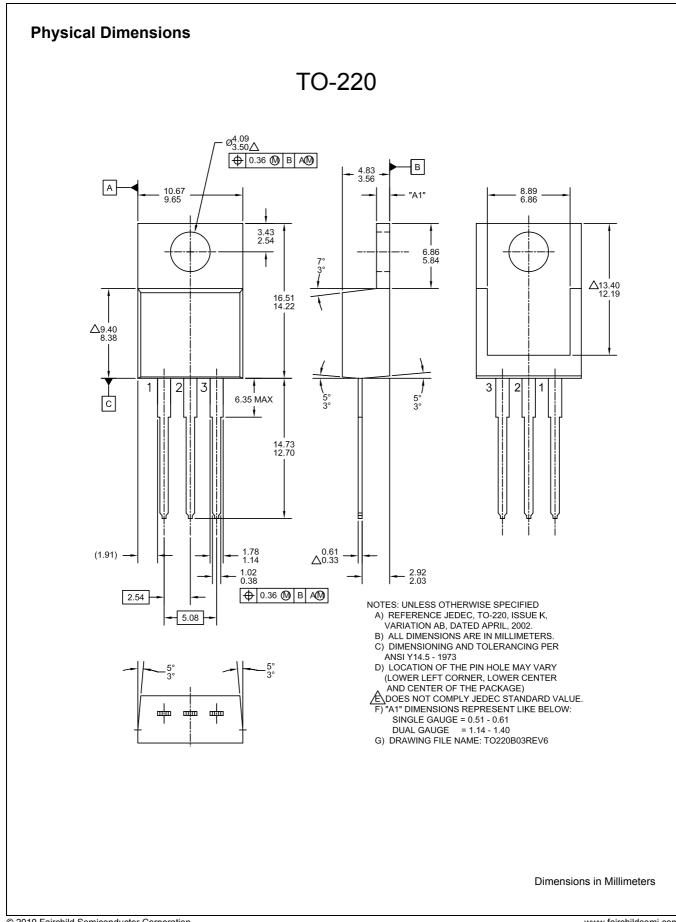


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